TOSHIBA 1SS397

### TOSHIBA DIODE SILICON EPITAXIAL PLANAR DIODE

# 155397

HIGH VOLTAGE, HIGH SPEED SWITCHING APPLICATIONS.

• Low Forward Voltage : V<sub>F</sub>=1.0V (Typ.)

• High Voltage : V<sub>R</sub>=400V (Min.)

• Fast Reverse Recovery Time :  $t_{rr} = 0.5 \mu s$  (Typ.)

• Small Total Capacitance : C<sub>T</sub>=2.5pF (Typ.)

• Small Package : SC-70

#### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	$v_{RM}$	420	V	
Reverse Voltage	$V_{\mathbf{R}}$	400	V	
Maximum (Peak) Forward Current	I <sub>FM</sub> 300		mA	
Average Forward Current	IO	100	mA	
Surge Current (10ms)	$I_{FSM}$	2	Α	
Power Dissipation	P	100	mW	
Junction Temperature	Tj	125	°C	
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C	

2.1±0.1 1.25±0.1 1.00-E 1.0

Unit in mm

EIAJ SC-70 TOSHIBA 1-2P1D

Weight: 0.006g

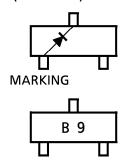
**JEDEC** 

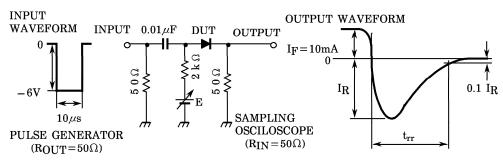
#### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V <sub>F(1)</sub>	$I_{\mathbf{F}} = 10 \text{mA}$	-	0.8	_	V
	$V_{F(2)}$	$I_{ m F}$ = 100mA	_	1.0	1.3	
Reverse Current	$I_{R(1)}$	$V_R = 300V$	_	_	0.1	$\mu$ A
	I <sub>R (2)</sub>	$V_R = 400V$	_	_	1.0	
Total Capacitance	$\mathbf{C_T}$	$V_R=0$ , f=1MHz	_	2.5	5.0	pF
Reverse Recovery Time	t <sub>rr</sub>	$I_{\mathbf{F}} = 10 \text{mA}$ (Fig.1)	_	0.5	_	μs

## EQUIVALENT CIRCUIT (TOP VIEW)

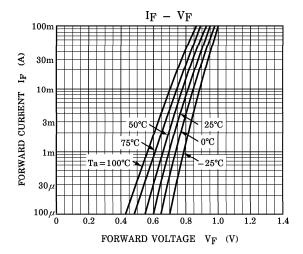
Fig1. REVERSE RECOVERY TIME ( $t_{rr}$ ) TEST CIRCUIT

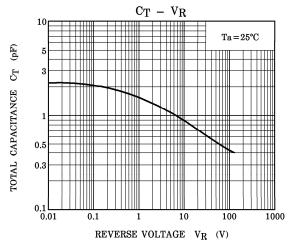


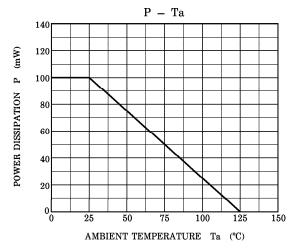


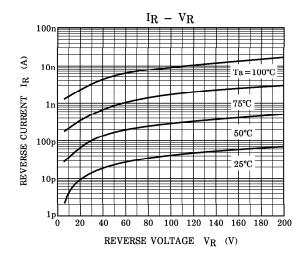
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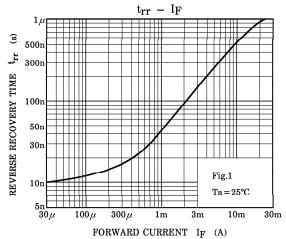
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